

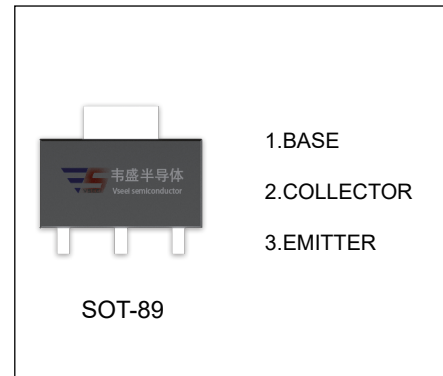
BST52 TRANSISTOR (NPN)

FEATURES

- Low Voltage
- High Current
- Integrated Diode and Resistor

APPLICATIONS

- Industrial Switching Applications: Print Hammer, Solenoid, Relay and Lamp Driving



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	90	V
V_{CEO}	Collector-Emitter Voltage	80	V
I_C	Collector Current	500	mA
P_C	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	$^{\circ}\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	90			V
Collector-emitter sustain voltage	V_{CES}	$V_{BE}=0, I_C=100\mu\text{A}$	80			V
Collector cut-off current	I_{CES}	$V_{BE}=0, V_{CE}=80\text{V}$			50	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			50	nA
DC current gain	h_{FE}	$V_{CE}=10\text{V}, I_C=150\text{mA}$	1000			
		$V_{CE}=10\text{V}, I_C=500\text{mA}$	2000			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}, I_B=0.5\text{mA}$			1.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=500\text{mA}, I_B=0.5\text{mA}$			1.9	V
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=500\text{mA}, f=100\text{MHz}$		200		MHz